

N-channel 30 V 3.5mΩ logic level MOSFET in LFPAK using NextPower technology

Rev. 01 — 2 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance

1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing

1.4 Quick reference data

Table 1. Quick reference data

Symbol Parameter Conditions Min Тур Max Unit 25 °C ≤ T_i ≤ 175 °C ٧ VDS drain-source voltage 30 _ -[1] - I_D drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ 100 А see Figure 1 **P**_{tot} total power dissipation T_{mb} = 25 °C; see Figure 2 92 W --T_i junction temperature -55 °С -175 **Static characteristics** drain-source on-state $V_{GS} = 4.5 \text{ V}; I_{D} = 25 \text{ A};$ 3.75 4.55 mΩ R_{DSon} resistance $T_i = 25 \text{ °C}; \text{ see Figure 12}$ $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ 2.9 3.5 mΩ $T_i = 25 \text{ °C}; \text{ see Figure 12}$

- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads
- Server power supplies
- Sync rectifier



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Table 1.	QUICK reference datac	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynami	c characteristics					
Q _{GD}	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \; V; \; I_{D} = 25 \; A; \\ V_{DS} = 15 \; V; \; see \; \underline{Figure \; 14}; \\ see \; \underline{Figure \; 15} \end{array}$	-	4.1	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 25 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ $\text{see } \frac{\text{Figure } 15}{\text{Figure } 15}$	-	14.2	-	nC

Quick reference data continued Table 1

[1] Continuous current is limited by package.

Pinning information 2.

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK;	

Power-SO8)

Ordering information 3.

Table 3. Ordering	ing information			
Type number	Package			
	Name	Description	Version	
PSMN3R2-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669	

Marking 4.

Table 4.	Marking codes	
Type number		Marking code ^[1]
PSMN3R2-30YLC		3C230L

[1] % = placeholder for manufacturing site code

PSMN3R2-30YLC

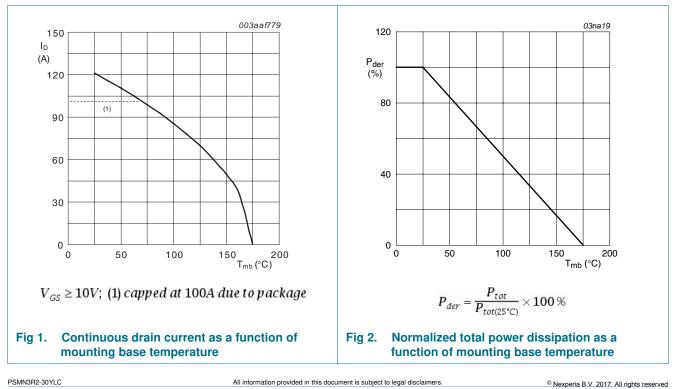
5. Limiting values

Table 5. Limiting values

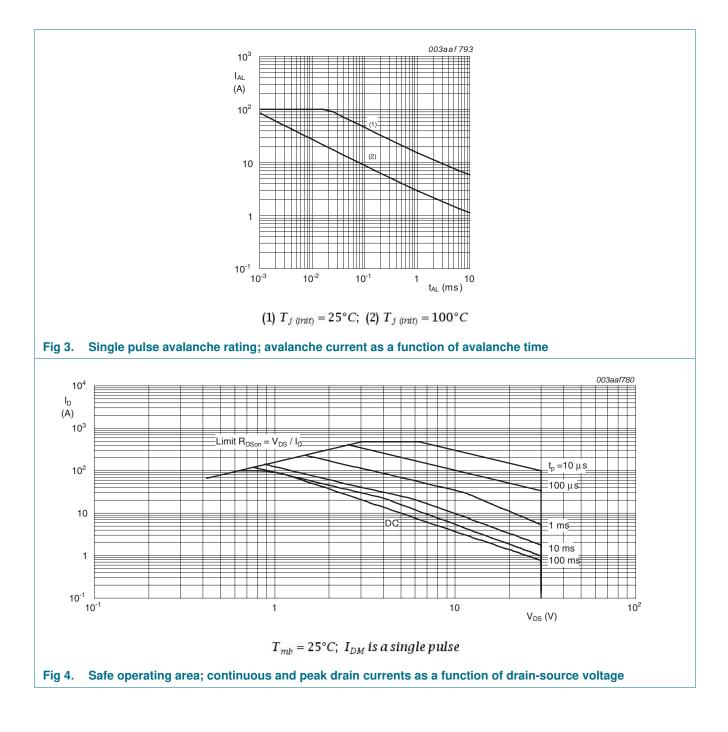
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	100	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	85	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	482	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	92	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	360	-	V
Source-drain	n diode				
ls	source current	T _{mb} = 25 °C	-	83	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	482	А
Avalanche ru	ıggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_{D} = 100 \text{ A}; \\ V_{sup} \leq 30 \text{ V}; R_{GS} = 50 \Omega; \text{ unclamped}; \\ \text{see } \underline{\text{Figure 3}} \end{array} $	-	39	mJ

[1] Continuous current is limited by package.



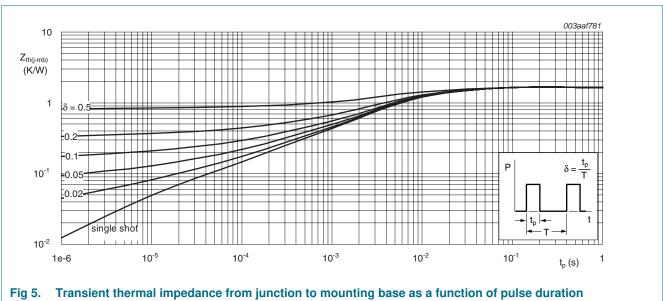
PSMN3R2-30YLC



6. Thermal characteristics

R _{th(j-mb)} thermal resistance from junction to mounting see Figure 5 - 1.46 1.64 K/W base	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	$R_{th(j-mb)}$		see <u>Figure 5</u>	-	1.46	1.64	K/W

Table 6. Thermal characteristics



7. Characteristics

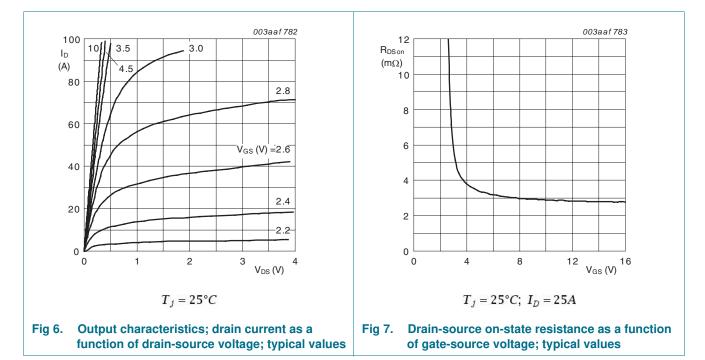
Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 10;</u> see <u>Figure 11</u>	1.05	1.53	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; see Figure 12	-	3.75	4.55	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	7.45	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 12	-	2.9	3.5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 150 °C; see Figure 12; see Figure 13	-	-	5.8	mΩ
R _G	gate resistance	f = 1 MHz	-	2	4	Ω
Dynamic	characteristics					
$Q_{G(tot)}$ total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	29.5	-	nC	
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	14.2	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	29	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15	-	3.9	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	3	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.9	-	nC
Q _{GD}	gate-drain charge		-	4.1	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see $\frac{\text{Figure } 15}{\text{Figure } 15}$	-	2.27	-	V
C _{iss}	input capacitance	V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz;	-	2081	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	432	-	pF
C _{rss}	reverse transfer capacitance		-	141	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω; V_{GS} = 4.5 V;	-	19.5	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	31	-	ns
t _f	fall time		-	14	-	ns

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Product data sheet

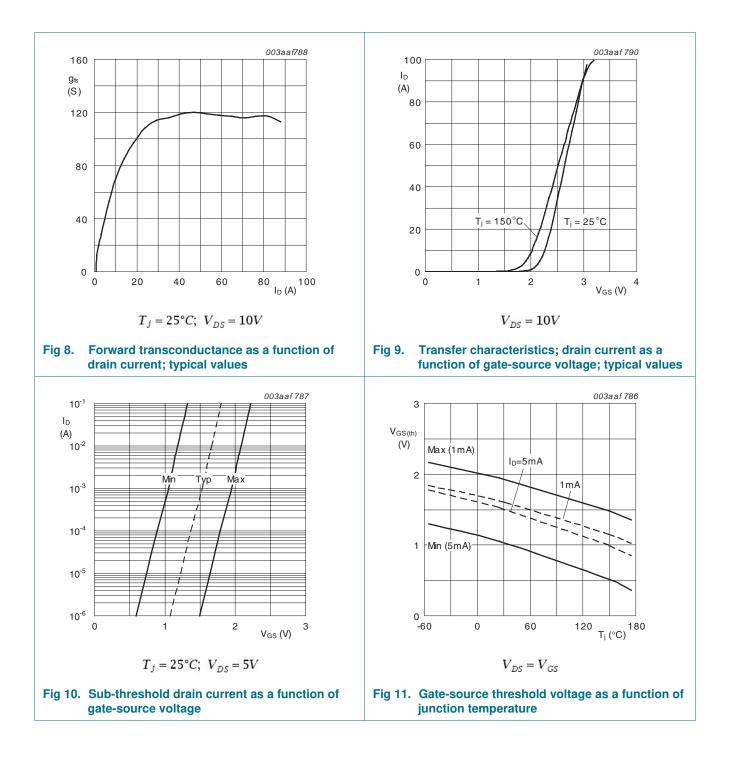
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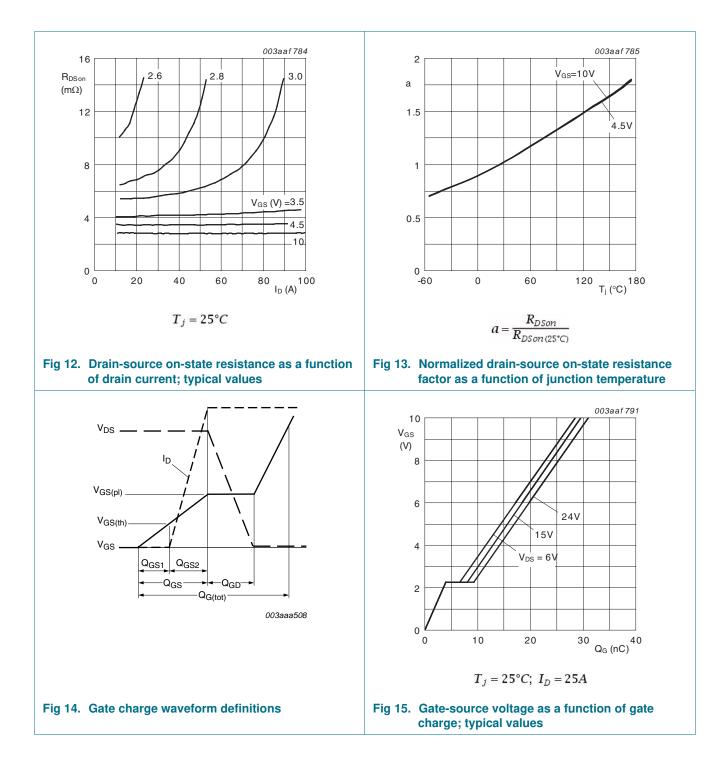
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V_{GS} = 0 V; V_{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	12.2	-	nC
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.1	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	27	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	19.5	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 V; I_S = 25 A;$	-	15	-	ns
t _b	reverse recovery fall time	dl _S /dt = -100 A/μs; V _{DS} = 15 V; see <u>Figure 18</u>	-	12	-	ns



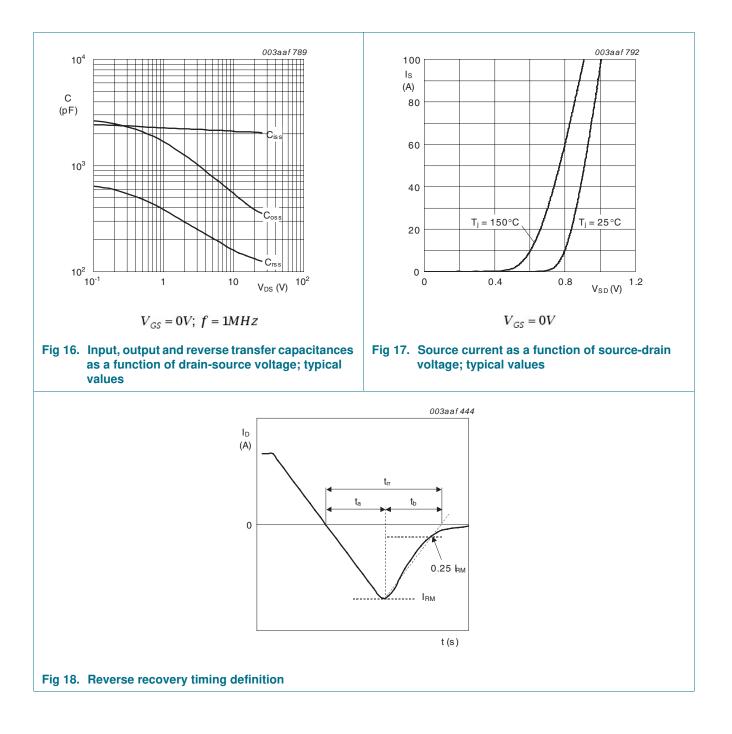
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8. Package outline

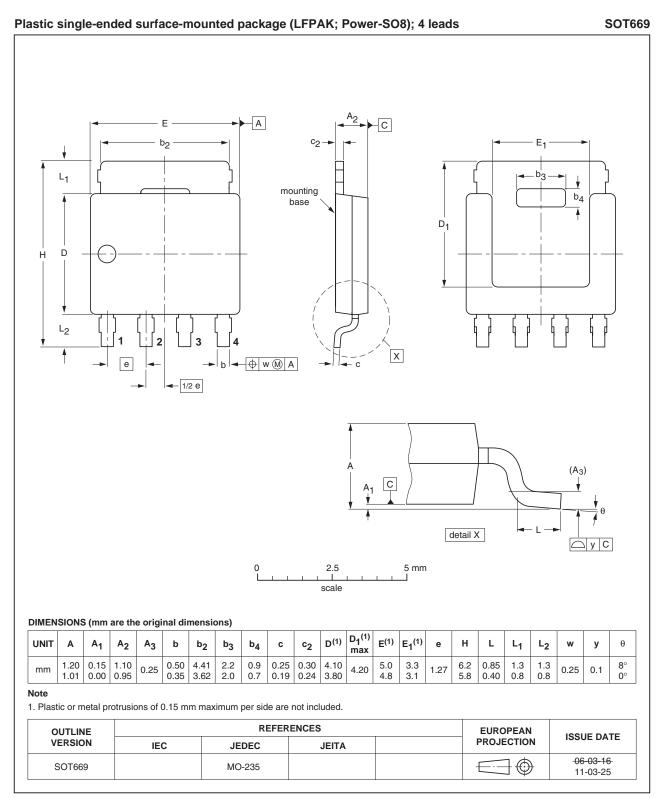


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN3R2-30YLC Product data sheet

9. Revision history

Table 8. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R2-30YLC v.1	20110502	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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